

SINGLE 2 INPUT POSITIVE NAND GATE

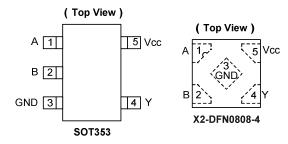
Description

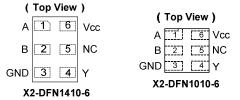
The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

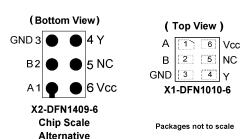
The 74AUP1G00 is a single two-input positive NAND gate with a standard push-pull output designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing damaging current backflow when the device is powered down. The gate performs the positive Boolean function:

$$Y = \overline{A \bullet B}$$
 or $Y = \overline{A} + \overline{B}$

Pin Assignments







Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4 mA Output Drive at 3.0V
- Low Static Power Consumption

 $I_{CC} < 0.9 \mu A$

• Low Dynamic Power Consumption

C_{PD} = 6pF (Typical at 3.6V)

- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250mV at V_{CC} = 3.0V.
- IOFF Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22

2000-V Human Body Model (A114)

Exceeds 1000-V Charged Device Model (C101)

- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages Named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

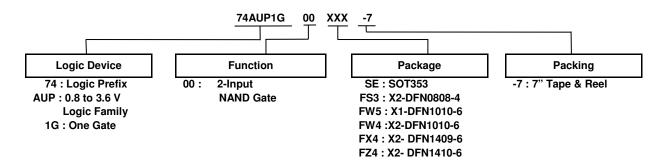
- Suited for Battery and Low Power Needs
- Wide array of products such as:
 - Tablets, E-readers
 - Cell Phones, Personal Navigation / GPS
 - MP3 Players ,Cameras, Video Recorders
 - PCs, Ultrabooks, Notebooks, Netbooks
 - Computer Peripherals, Hard Drives, SSDs, CD/DVD ROMs
 - TVs, DVDs, DVRs, Set-Top Boxes

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Ordering Information



Device	Package	Package	Package	7" Tape	and Reel
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix
74AUP1G00SE-7	SE	SOT353	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7
74AUP1G00FS3-7	FS3	X2-DFN0808-4	0.8mm x 0.8mm x 0.35mm 0.5 mm pad pitch (diamond)	5,000/Tape & Reel	-7
74AUP1G00FW5-7	FW5	X1-DFN1010-6	1.0mm x 1.0mm x 0.5mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G00FW4-7	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G00FX4-7	FX4	X2-DFN1409-6 Chip Scale Alternative	1.4mm x 0.9mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G00FZ4-7	FZ4	X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Pin Descriptions

Pin Name	Function
Α	Data Input
В	Data Input
GND	Ground
Υ	Data Output
V _{CC}	Supply Voltage

Logic Diagram



Function Table

Inp	uts	Output
Α	В	Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

^{5.} The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.



Absolute Maximum Ratings (Notes 6 & 7) (@T_A = +25 °C, unless otherwise specified.)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I < 0	50	mA
l _{OK}	Output Clamp Current (V _O < 0)	50	mA
lo	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
I _{CC}	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	℃
T _{STG}	Storage Temperature	-65 to +150	℃

Notes:

Recommended Operating Conditions (Note 8) (@T_A = +25 ℃, unless otherwise specified.)

Symbol	Pa	arameter	Min	Max	Unit
Vcc	Operating Voltage		0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	V _{CC}	V
		V _{CC} = 0.8V	_	-20	μΑ
		V _{CC} = 1.1V	_	-1.1	
	High Lovel Output Current	V _{CC} = 1.4V	_	-1.7	
Гон	High-Level Output Current	V _{CC} = 1.65V	_	-1.9	mA
		V _{CC} = 2.3V	_	-3.1	
		V _{CC} = 3.0V	_	-4	
		V _{CC} = 0.8V	_	20	μΑ
		V _{CC} = 1.1V	_	1.1	
	Low-Level Output Current	V _{CC} = 1.4V	_	1.7	
l _{OL}	Low-Level Output Current	V _{CC} = 1.65V	_	1.9	mA
		V _{CC} = 2.3V	_	3.1	
		V _{CC} = 3.0V	_	4	
Δt/ΔV	Input Transition Rise or Fall Rate V _{CC} = 0.8V to 3.6V		_	200	ns/V
TA	Operating Free-Air Temperature		-40	125	℃

Note: 8. Unused inputs should be held at V_{CC} or Ground.

^{6.} Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

^{7.} Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



Electrical Characteristics (@T_A = +25 ℃, unless otherwise specified.)

Cumabal	Davamatav	Took Conditions		T _A = -	+25°C	T _A = -40 ℃	C to +85°C	Unit
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Min	Max	Unit
		_	0.8V to 1.65V	0.80 x V _{CC}	_	0.80 x V _{CC}	_	
.,,	High-Level Input	_	1.65V to 1.95V	0.65 x V _{CC}	_	0.65 x V _{CC}	_	v
V _{IH}	Voltage	_	2.3V to 2.7V	1.6	_	1.6	_	·
		_	3.0V to 3.6V	2.0	_	2.0	_	
		_	0.8V to 1.65V	_	0.30 x V _{CC}	_	0.30 x V _{CC}	
V _{IL}	Low-Level Input	_	1.65V to 1.95V	_	0.35 x V _{CC}	_	0.35 x V _{CC}	v
VIL	Voltage	_	2.3V to 2.7V	_	0.7	_	0.7	V
		_	3.0V to 3.6V	_	0.9		0.9	
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V _{CC} - 0.1	_	$V_{CC} - 0.1$	_	
		I _{OH} = -1.1mA	1.1V	0.75 x V _{CC}	_	0.7 x V _{CC}	_	
		I _{OH} = -1.7mA	1.4V	1.11	_	1.03	_	
.,	High-Level Output	I _{OH} = -1.9mA	1.65V	1.32	_	1.3	_	.,
VOH	V _{OH} Voltage	I _{OH} = -2.3mA	0.01/	2.05	_	1.97	_	V
		I _{OH} = -3.1mA	2.3V	1.9	_	1.85	_	
		I _{OH} = -2.7mA	2)./	2.72	_	2.67	_	
		I _{OH} = -4mA	- 3V	2.6	_	2.55	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.1	_	0.1	
		I _{OL} = 1.1mA	1.1V	_	0.3 x V _{CC}	_	0.3 x V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.31		0.37	
	Low-Level Output	I _{OL} = 1.9mA	1.65V	_	0.31	_	0.35	
V_{OL}	Voltage	I _{OL} = 2.3mA		_	0.31	_	0.33	V
		I _{OL} = 3.1mA	2.3V	_	0.44	_	0.45	
		I _{OL} = 2.7mA		_	0.31	_	0.33	
		I _{OL} = 4mA	3V	_	0.44	_	0.45	
I ₁	Input Current	A or B Input V _I = GND to 3.6V	0 to 3.6V	_	± 0.1	_	± 0.5	μΑ
loff	Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0	_	0.2	_	0.6	μΑ
Δl _{OFF}	Delta Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0 V to 0.2V	_	0.2	_	0.6	μΑ
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8 V to 3.6V	_	0.5	_	0.9	μΑ
ΔI _{CC}	Additional Supply Current	One Input at V _{CC} -0.6V Other Inputs at V _{CC} or GND	3.3V	_	40	_	50	μА



Electrical Characteristics (continued) (@T_A = +25 °C, unless otherwise specified.)

Cymphol	Parameter	Test Conditions	V	T _A = -40 ℃	to +125℃	Unit
Symbol	Parameter	rest Conditions	V _{CC}	Min	Max	Oilit
		_	0.8V to 1.65V	0.80 x V _{CC}	_	
V _{IH}	High-Level Input Voltage	_	1.65V to 1.95V	0.70 x V _{CC}	_	V
VIH	ir light-Level input voltage	_	2.3V to 2.7V	1.6	_	V
		_	3.0V to 3.6V	2.0	_	
		_	0.8V to 1.65V	_	0.25 x V _{CC}	
V _{IL}	Low-Level Input Voltage	_	1.65V to 1.95V	_	0.30 x V _{CC}	V
V IL	Low Level Input Voltage	_	2.3V to 2.7V	_	0.7	•
		_	3.0V to 3.6V	_	0.9	
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V _{CC} - 0.11	_	
		I _{OH} = -1.1mA	1.1V	0.6 x V _{CC}	_	-
		I _{OH} = -1.7mA	1.4V	0.93	_	
V	Lligh Lavel Output Valtage	I _{OH} = -1.9mA	1.65V	1.17	_	V
V _{OH}	High-Level Output Voltage	I _{OH} = -2.3mA	0.01/	1.77	_	V
		I _{OH} = -3.1mA	2.3V	1.67	_	
		I _{OH} = -2.7mA	0)/	2.40	_	
		I _{OH} = -4mA	3V	2.30	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.11	
		I _{OL} = 1.1mA	1.1V	_	0.33 x V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.41	
		I _{OL} = 1.9mA	1.65V	_	0.39	.,
V _{OL}	Low-Level Output Voltage	I _{OL} = 2.3mA	2.01/	_	0.36	V
		I _{OL} = 3.1mA	2.3V	_	0.50	
		I _{OL} = 2.7mA		<u> </u>	0.36	
		I _{OL} = 4mA	3V	_	0.50	
II	Input Current	A or B Input, V _I = GND to 3.6V	0 to 3.6V	_	± 0.75	μA
l _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0	-	± 3.5	μA
Δl _{OFF}	Delta Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μA
ΔI _{CC}	Additional Supply Current	Input at V _{CC} -0.6V Other Inputs at V _{CC} or GND	3.3V	_	75	μΑ



Switching Characteristics

 $C_L = 5pF$, See Figure 1

Parameter	From	TO OUTPUT	V	1	T _A = +25°C		T _A = -40 °C to +85 °C		T _A = -40 °C to +125 °C		Unit
Farailleter	Input		V _{cc}	Min	Тур	Max	Min	Max	Min	Max	Unit
			V8.0	_	17.5	_	_	_	_	_	
		Y	1.2V ± 0.1V	2.5	5.3	11.0	2.1	12.2	2.1	13.5	
	A or B		1.5V ± 0.1V	2.0	3.8	6.8	1.8	7.8	1.8	8.6	
t _{pd}	AOID		1.8V ± 0.15V	1.6	3.1	5.3	1.4	6.2	1.4	6.9	ns
			2.5V ± 0.2V	1.3	2.5	4.0	1.1	4.7	1.1	5.2	
			$3.3V \pm 0.3V$	1.0	2.2	3.6	1.0	4.2	1.0	4.7	

C_L = 10pF, See Figure 1

Parameter	From Input	TO OUTPUT	.,	1	T _A = +25 ℃		T _A = -40 °C to +85 °C		T _A = -40 °C to +125 °C		Unit
raiailletei			Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
			V8.0	_	21.0	_	_	_	_	_	
			1.2V ± 0.1V	2.4	6.1	13.0	2.2	14.4	2.2	15.9	ns
	A or B	V	1.5V ± 0.1V	2.4	4.4	7.9	2.2	9.2	2.2	10.2	
t _{pd}	AUID	Ť	1.8V ± 0.15V	2.0	3.7	6.2	1.9	7.3	1.9	8.1	
		-	2.5V ± 0.2V	1.4	3.0	4.7	1.3	5.6	1.3	6.2	
			$3.3V \pm 0.3V$	1.3	2.8	4.3	1.2	4.9	1.2	5.4	

 $C_L = 15pF$, See Figure 1

Parameter	From Input	TO OUTPUT	V	T _A = +25 ℃			T _A = -40 °C to +85 °C		T _A = -40 °C to +125 °C		Unit
Parameter			V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Unit
		V8.0	_	24.5	_	_	_	_	_		
			1.2V ± 0.1V	3.4	6.9	14.8	3.1	16.5	3.1	18.2	ns
	A or B	V	1.5V ± 0.1V	2.8	5.0	8.9	2.5	10.5	2.5	11.6	
t _{pd}	AUID	Y	1.8V ± 0.15V	2.0	4.1	7.0	2.0	8.3	2.0	9.2	
			2.5V ± 0.2V	1.7	3.5	5.3	1.5	6.4	1.5	7.1	
			$3.3V \pm 0.3V$	1.6	3.2	4.9	1.4	5.7	1.4	6.3	

C_L = 30pF, See Figure 1

Donomoton	From Input	TO OUTPUT	V	T _A = +25 ℃			T _A = -40 °C to +85 °C		T _A = -40 °C to +125 °C		Unit
Parameter			V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Unit
			V8.0	_	34.8	_	_	_	_	_	
			1.2V ± 0.1V	4.6	17.5	22.0	4.1	22.6	4.1	24.9	ns
	A or B	V	1.5V ± 0.1V	3.0	6.5	11.8	2.9	14.0	2.9	15.4	
t _{pd}	AUID	T T	1.8V ± 0.15V	2.6	5.4	9.3	2.3	11.1	2.3	12.3	
		-	2.5V ± 0.2V	2.4	4.6	7.1	2.1	8.5	2.1	9.4	
			3.3V ± 0.3V	2.3	2.6	6.5	2.1	7.6	2.1	8.4	



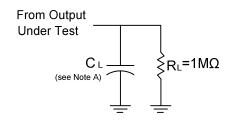
Operating and Package Characteristics (@T_A = +25 ℃, unless otherwise specified.)

	Parameter	Test Conditio	ns	V _{CC}	Тур	Unit
				0.8V	6.5	
				1.2V ± 0.1V	6.3	
_	Power Dissipation	f = 1MH	lz	1.5V ± 0.1V	6.3	
C_{pd}	Capacitance	No Loa	d	1.8V ± 0.15V	6.2	pF
				2.5V ± 0.2V	6.2	
				3.3V ± 0.3V	6.1	
Ci	Input Capacitance	$V_i = V_{CC}$ or	GND	0V or 3.3V	1.5	pF
		SOT353		_	371	
		X2-DFN0808-4		_	430	
	Thermal Resistance	X1-DFN1010-6	(NI=4= 0)	_	435	°C/W
θ_{JA}	Junction-to-Ambient	X2-DFN1010-6	(Note 9)	_	445	- °C/W
		X2-DFN1409-6		_	470	
		X2-DFN1410-6		_	460	
		SOT353		_	143	
		X2-DFN0808-4		_	240	
0	Thermal Resistance	X1-DFN1010-6	(Nata 0)	_	250	00.444
θJC	Junction-to-Case	X2-DFN1010-6	(Note 9)	_	250	°C/W
		X2-DFN1409-6		_	275	
		X2-DFN1410-6		_	265	

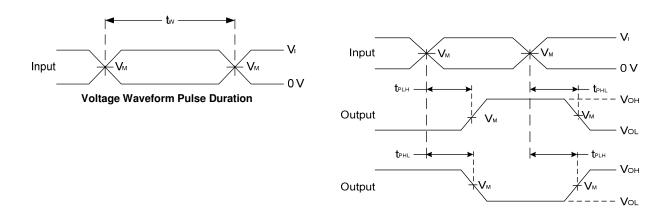
Note: 9. Test condition for each of the six package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Parameter Measurement Information



Vac	Inputs		V	•
Vcc	VI	t _r /t _f	V_{M}	CL
0.8V	Vcc	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V±0.1V	Vcc	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V±0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ±0.15V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V±0.2V	Vcc	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V±0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF



Inverting and Non Inverting Outputs

Voltage Waveform Propagation Delay Times

Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

B. All pulses are supplied at pulse repetition rate ≤ 10MHz.

- C. Inputs are measured separately one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as t_{PD}.



Marking Information

(1) SOT353

(Top View)

4 XX Y WX2 3

XX: Identification code

Y: Year 0~9

W: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents 52 and 53 week

 \underline{X} : A $^{\sim}$ Z: Internal code

Part Number	Package	Identification Code
74AUP1G00SE-7	SOT353	XH

(2) X2-DFN0808-4, X1-DFN1010-6, X2-DFN1010-6, X2-DFN1409-6 and X2-DFN1410-6

(Top View)

XX $\underline{Y} \underline{W} \underline{X}$ XX: Identification Code

Y: Year: 0~9

 $\overline{\mathbf{W}}$: Week: A~Z: 1~26 week;

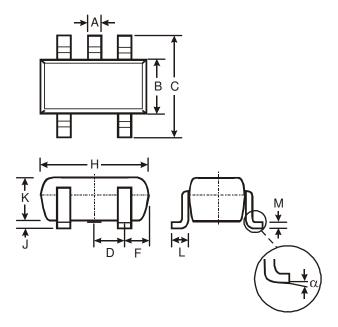
a~z: 27~52 week; z represents 52 and 53 week

X: A~Z: Internal code

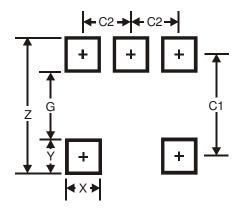
Part Number	Package	Identification Code
74AUP1G00FS3-7	X2-DFN0808-4	YJ
74AUP1G00FW5-7	X1-DFN1010-6	Q1
74AUP1G00FW4-7	X2-DFN1010-6	XH
74AUP1G00FX4-7	X2-DFN1409-6	HA
74AUP1G00FZ4-7	X2-DFN1410-6	XH



SOT353 Package Outline Dimensions and Suggested Pad Layout



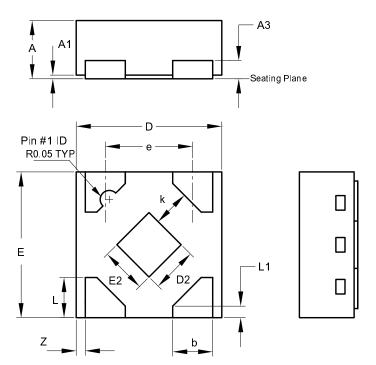
SOT353				
Dim	Min	Max	Тур	
Α	0.10	0.30	0.25	
В	1.15	1.35	1.30	
С	2.00	2.20	2.10	
D		0.65 Typ	כ	
F	0.40	0.45	0.425	
Н	1.80	2.20	2.15	
J	0	0.10	0.05	
K	0.90	1.00	1.00	
L	0.25	0.40	0.30	
М	0.10	0.22	0.11	
α	0°	8°	-	
All Dimensions in mm				



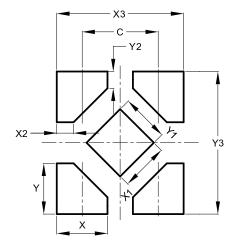
Dimensions	Value (in mm)	
Z	2.5	
G	1.3	
Х	0.42	
Υ	0.6	
C1	1.9	
C2	0.65	



X2-DFN0808-4 Package Outline Dimensions and Suggested Pad Layout



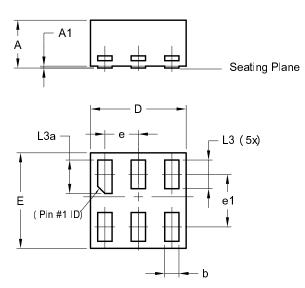
	X2-DFN0808-4				
Dim	Min	Max	Тур		
Α	0.25	0.35	0.30		
A1	0	0.04	0.02		
A3	-	-	0.13		
b	0.17	0.27	0.22		
D	0.75	0.85	0.80		
D2	0.15	0.35	0.25		
E	0.75	0.85	0.80		
E2	0.15	0.35	0.25		
е	-	-	0.48		
k	0.20	-	-		
L	0.17	0.27	0.22		
L1	0.02	0.12	0.07		
Z	-	-	0.05		
Α	All Dimensions in mm				



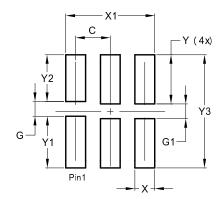
Dimensions	Value
С	0.480
X	0.320
X1	0.300
X2	0.106
Х3	0.800
Υ	0.320
Y1	0.300
Y2	0.106
Y3	0.900



X1-DFN1010-6 (Type B) Package Outline Dimensions and Suggested Pad Layout



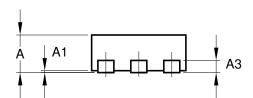
	X1-DFN1010-6 (Type B)				
Dim	Min	Max	Тур		
Α	-	0.50	0.39		
A1	-	0.04	-		
b	0.12	0.20	0.15		
D	0.95	1.050	1.00		
Е	0.95	1.050	1.00		
е	0.35 BSC				
e1		0.55 BSC			
L3	0.27	0.30	0.30		
L3a	0.32	0.40	0.35		
All	All Dimensions in mm				

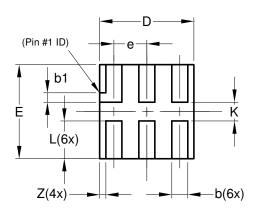


Dimensions	Value	
Dillielisions	(in mm)	
С	0.350	
G	0.150	
G1	0.150	
Х	0.200	
X1	0.900	
Υ	0.500	
Y1	0.525	
Y2	0.475	
Y3	1.150	

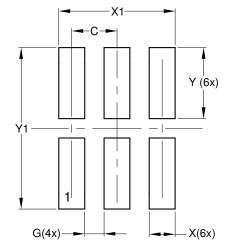


X2-DFN1010-6 Package Outline Dimensions and Suggested Pad Layout





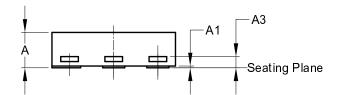
X2-DFN1010-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
A 1	0.00	0.05	0.02	
A3	_	_	0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
E	0.95	1.05	1.00	
е	_	_	0.35	
L	0.35	0.45	0.40	
K	0.15	_		
Z	_		0.065	
All Dimensions in mm				

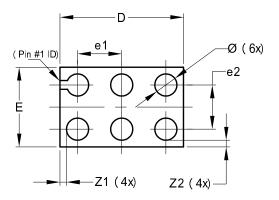


Dimensions	Value (in mm)	
С	0.350	
G	0.150	
Х	0.200	
X1	0.900	
Υ	0.550	
Y1	1.250	

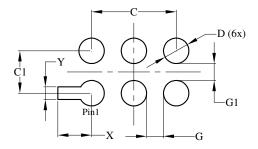


X2-DFN1409-6 Package Outline Dimensions and Suggested Pad Layout





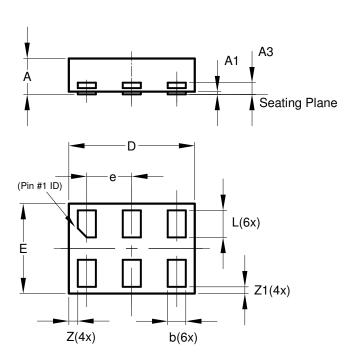
X2-DFN1409-6			
Dim	Min	Max	Тур
Α	-	0.40	0.39
A1	0	0.05	0.02
A 3	-	1	0.13
Ø	0.20	0.30	0.25
D	1.35	1.45	1.40
Е	0.85	0.95	0.90
e1	-	-	0.50
e2	-	-	0.50
Z 1	-	-	0.075
Z 2	-	-	0.075
All Dimensions in mm			



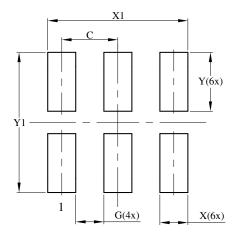
Dimensions	Value (in mm)
С	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
Х	0.400
Υ	0.150



X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout



X2-DFN1410-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3			0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е			0.50	
L	0.25	0.35	0.30	
Z			0.10	
Z 1	0.045	0.105	0.075	
All Dimensions in mm				



Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Υ	0.525
Y1	1.250



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